DATA SHEET

74LVC2245A

Octal transceiver with direction pin, 30 Ω series termination resistors; 5 V tolerant input/output; 3-state

Product specification
Supersedes data of 2002 Jun 10

2003 Nov 17

Philips Semiconductors

PHILIPS

Octal transceiver with direction pin, 30 Ω series termination resistors; 5 V tolerant input/output; 3-state

74LVC2245A

FEATURES

- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 to 3.6 V
- CMOS low power consumption
- Direct interface with TTL levels
- Inputs accept voltages up to 5.5 V
- Integrated 30 Ω termination resistors
- Complies with JEDEC standard no. 8-1A
- ESD protection:
  HBM EIA/JESD22-A114-A exceeds 2000 V
  MM EIA/JESD22-A115-A exceeds 200 V.
- Specified from –40 to +85 °C and –40 to +125 °C.

DESCRIPTION

The 74LVC2245A is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 or 5 V devices. In 3-state operation, outputs can handle 5 V. These features allow the use of these devices as translators in a mixed 3.3 and 5 V environment.

The 74LVC2245A is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions.

The 74LVC2245A features an output enable ($\overline{OE}$) input for easy cascading and a send/receive (DIR) input for direction control. $\overline{OE}$ controls the outputs so that the buses are effectively isolated.

The 74LVC2245A is designed with 30 Ω series termination resistors in both HIGH and LOW output stages to reduce line noise.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; $t_r = t_f \leq 2.5$ ns.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t_{PHL}/t_{PLH}	propagation delay A_n to B_n, B_n to A_n	C_L = 50 pF; V_{CC} = 3.3 V	3.6	ns
C_I	input capacitance		4.0	pF
C_{PD}	power dissipation capacitance per buffer	V_{CC} = 3.3 V; notes 1 and 2	13	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
   $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
   f_i = input frequency in MHz;
   f_o = output frequency in MHz;
   C_L = output load capacitance in pF;
   V_{CC} = supply voltage in Volts;
   N = total load switching outputs;
   $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.
2. The condition is V_I = GND to V_{CC}.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE				
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE
74LVC2245AD	−40 to +125 °C	20	SO20	plastic	SOT163-1
74LVC2245ADB	−40 to +125 °C	20	SSOP20	plastic	SOT339-1
74LVC2245APW	−40 to +125 °C	20	TSSOP20	plastic	SOT360-1
74LVC2245ABQ	−40 to +125 °C	20	DHVQFN20	plastic	SOT764-1

FUNCTION TABLE

See note 1.

INPUT		INPUT/OUTPUT	
$\overline{OE}$	DIR	An	Bn
L	L	A = B	input
L	H	input	B = A
H	X	Z	Z

Note

1. H = HIGH voltage level;
   L = LOW voltage level;
   X = don't care;
   Z = high-impedance OFF-state.

PINNING

PIN	SYMBOL	DESCRIPTION
1	DIR	direction control input
2	A0	data input/output
3	A1	data input/output
4	A2	data input/output
5	A3	data input/output
6	A4	data input/output
7	A5	data input/output
8	A6	data input/output
9	A7	data input/output
10	GND	ground (0 V)

PIN	SYMBOL	DESCRIPTION
11	B7	data input/output
12	B5	data input/output
13	B5	data input/output
14	B4	data input/output
15	B3	data input/output
16	B2	data input/output
17	B1	data input/output
18	B0	data input/output
19	$\overline{OE}$	output enable input (active LOW)
20	V_{CC}	supply voltage

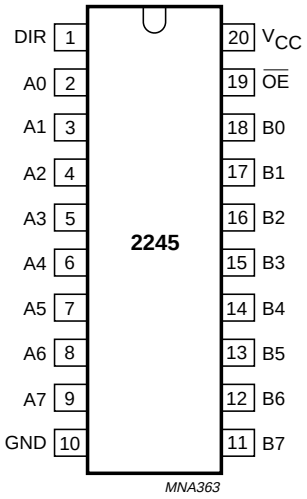
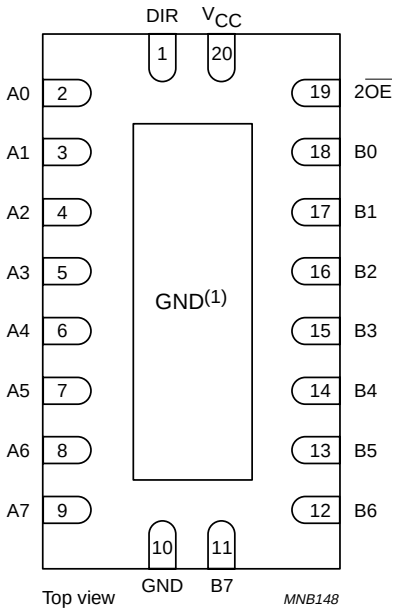


Fig.1 Pin configuration SO20 and (T)SSOP20.



(1) The die substrate is attached to this pad using conductive die attach material. It can not be used as a supply pin or input.

Fig.2 Pin configuration DHVQFN20.

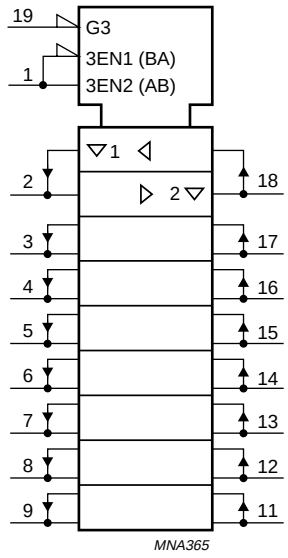


Fig.3 Logic symbol (IEEE/IEC).

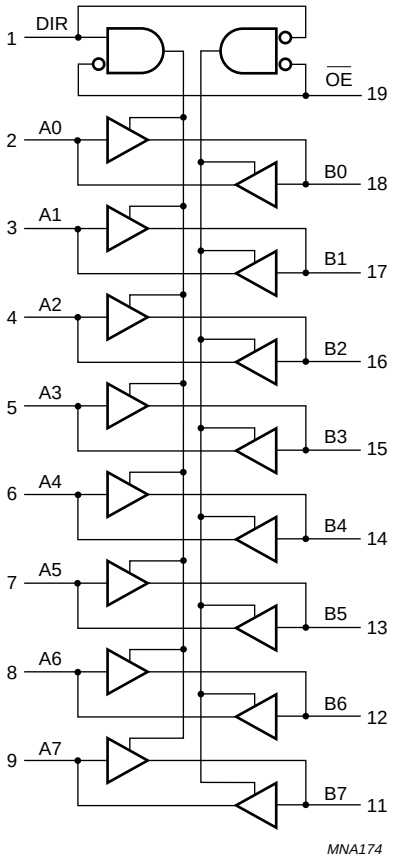


Fig.4 Logic symbol.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage	for maximum speed performance	2.7	3.6	V
		for low-voltage applications	1.2	3.6	V
V_I	input voltage		0	5.5	V
V_O	output voltage	output HIGH or LOW state	0	V_{CC}	V
		output 3-state	0	5.5	V
T_{amb}	ambient temperature		–40	+125	°C
t_r, t_f	input rise and fall times	V_{CC} = 1.2 to 2.7 V	0	20	ns/V
		V_{CC} = 2.7 to 3.6 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		–0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$	–	–50	mA
V_I	input voltage	note 1	–0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$	–	±50	mA
V_O	output voltage	output HIGH or LOW state; note 1	–0.5	V_{CC} + 0.5	V
		output 3-state; note 1	–0.5	+6.5	V
I_O	output source or sink current	V_O = 0 to V_{CC}	–	±50	mA
I_{CC}, I_{GND}	V_{CC} or GND current		–	±100	mA
T_{stg}	storage temperature		–65	+150	°C
P_{tot}	power dissipation	T_{amb} = –40 to +125 °C; note 2	–	500	mW

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. For SO20 packages: above 70 °C derate linearly with 8 mW/K.
   For SSOP20 and TSSOP20 packages: above 60 °C derate linearly with 5.5 mW/K.
   For DHVQFN20 packages: above 60 °C derate linearly with 4.5 mW/K.

DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.(1)	MAX.	UNIT
		OTHER	V_{CC} (V)				
T_{amb} = −40 to +85 °C							
V_{IH}	HIGH-level input voltage		1.2	V_{CC}	–	–	V
			2.7 to 3.6	2.0	–	–	V
V_{IL}	LOW-level input voltage		1.2	–	–	0	V
			2.7 to 3.6	–	–	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}					
		I_O = −100 μA	2.7 to 3.6	V_{CC} − 0.2	V_{CC}	–	V
		I_O = −6 mA	2.7	V_{CC} − 0.5	–	–	V
		I_O = −12 mA	3.0	V_{CC} − 0.8	–	–	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}					
		I_O = 100 μA	2.7 to 3.6	–	0	0.2	V
		I_O = 6 mA	2.7	–	–	0.4	V
		I_O = 12 mA	3.0	–	–	0.55	V
I_{LI}	input leakage current	V_I = 5.5 V or GND	3.6	–	±0.1	±5	μA
I_{OZ}	3-state output OFF-state current	V_I = V_{IH} or V_{IL}; V_O = 5.5 V or GND	3.6	–	±0.1	±5	μA
I_{off}	power off leakage supply	V_I or V_O = 5.5 V	0.0	–	±0.1	±10	μA
I_{CC}	quiescent supply current	V_I = V_{CC} or GND; I_O = 0	3.6	–	0.1	10	μA
ΔI_{CC}	additional quiescent supply current per pin	V_I = V_{CC} − 0.6 V; I_O = 0	2.7 to 3.6	–	5	500	μA

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.(1)	MAX.	UNIT
		OTHER	V_{CC} (V)				
T_{amb} = −40 to +125 °C							
V_{IH}	HIGH-level input voltage		1.2	V_{CC}	–	–	V
			2.7 to 3.6	2.0	–	–	V
V_{IL}	LOW-level input voltage		1.2	–	–	0	V
			2.7 to 3.6	–	–	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}					
		I_O = −100 μA	2.7 to 3.6	V_{CC} − 0.3	–	–	V
		I_O = −6 mA	2.7	V_{CC} − 0.65	–	–	V
		I_O = −12 mA	3.0	V_{CC} − 1	–	–	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}					
		I_O = 100 μA	2.7 to 3.6	–	–	0.3	V
		I_O = 6 mA	2.7	–	–	0.6	V
		I_O = 12 mA	3.0	–	–	0.8	V
I_{LI}	input leakage current	V_I = 5.5 V or GND	3.6	–	–	±20	μA
I_{OZ}	3-state output OFF-state current	V_I = V_{IH} or V_{IL}; V_O = 5.5 V or GND	3.6	–	–	±20	μA
I_{off}	power off leakage supply	V_I or V_O = 5.5 V	0.0	–	–	±20	μA
I_{CC}	quiescent supply current	V_I = V_{CC} or GND; I_O = 0	3.6	–	–	40	μA
ΔI_{CC}	additional quiescent supply current per pin	V_I = V_{CC} − 0.6 V; I_O = 0	2.7 to 3.6	–	–	5000	μA

Note

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

AC CHARACTERISTICS

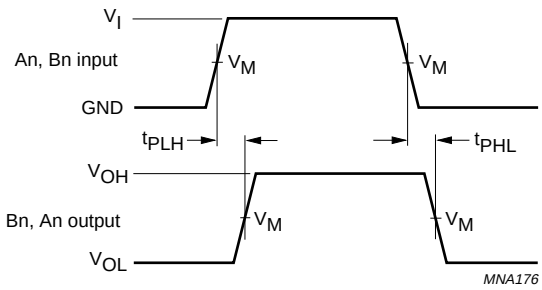
GND = 0 V; $t_r = t_f \leq 2.5$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	V_{CC} (V)				
T_{amb} = −40 to +85 °C							
t_{PHL}/t_{PLH}	propagation delay An to Bn; Bn to An	see Figs 5 and 7	1.2	–	26	–	ns
			2.7	1.5	4.0	7.3	ns
			3.0 to 3.6	1.5	3.6(1)	6.3	ns
t_{PZH}/t_{PZL}	3-state output enable time $\overline{OE}$ to An; $\overline{OE}$ to Bn	see Figs 6 and 7	1.2	–	28	–	ns
			2.7	1.5	5.9	9.5	ns
			3.0 to 3.6	1.5	4.3(1)	8.2	ns
t_{PHZ}/t_{PLZ}	3-state output disable time $\overline{OE}$ to An; $\overline{OE}$ to Bn	see Figs 6 and 7	1.2	–	12.0	–	ns
			2.7	1.5	3.8	6.9	ns
			3.0 to 3.6	1.7	3.4(1)	5.9	ns
$t_{sk(0)}$	skew	note 2		–	–	1.0	ns
T_{amb} = −40 to +125 °C							
t_{PHL}/t_{PLH}	propagation delay nAn to nYn	see Figs 5 and 7	1.2	–	13	–	ns
			2.7	1.5	4.5	9.5	ns
			3.0 to 3.6	1.5	3.6(1)	8.0	ns
t_{PZH}/t_{PZL}	3-state output enable time n$\overline{OE}$ to nYn	see Figs 6 and 7	1.2	–	20	–	ns
			2.7	1.5	5.9	12.0	ns
			3.0 to 3.6	1.5	4.3(1)	10.5	ns
t_{PHZ}/t_{PLZ}	3-state output disable time n$\overline{OE}$ to nYn	see Figs 6 and 7	1.2	–	10	–	ns
			2.7	1.5	3.8	9.0	ns
			3.0 to 3.6	1.7	3.4(1)	7.5	ns
$t_{sk(0)}$	skew	note 2		–	–	1.5	ns

Notes

1. Typical values are measured at V_{CC} = 3.3 V.
2. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

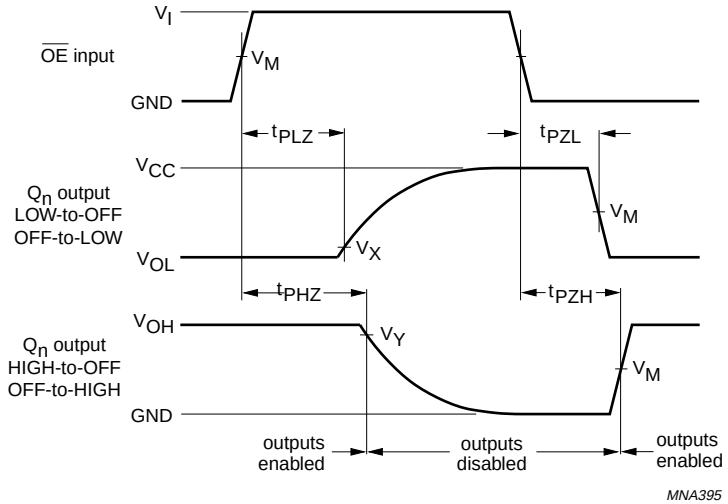
AC WAVEFORMS



V_{CC}	V_M	INPUT	
		V_I	$t_r = t_f$
1.2 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.5 ns
2.7 V	1.5 V	2.7 V	≤ 2.5 ns
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.5 The inputs An, Bn to outputs Bn, An propagation delays.

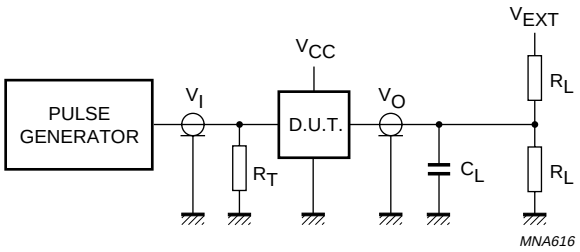


V_{CC}	V_M	INPUT	
		V_I	$t_r = t_f$
1.2 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.5 ns
2.7 V	1.5 V	2.7 V	≤ 2.5 ns
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns

$V_X = V_{OL} + 0.3$ V at $V_{CC} \geq 2.7$ V;
$V_X = V_{OL} + 0.1$ V at $V_{CC} < 2.7$ V;
$V_Y = V_{OH} - 0.3$ V at $V_{CC} \geq 2.7$ V;
$V_Y = V_{OH} - 0.1$ V at $V_{CC} < 2.7$ V.

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.6 3-state enable and disable times.



V_{CC}	V_I	C_L	R_L	V_{EXT}		
				t_{PLH}/t_{PHL}	t_{PZH}/t_{PHZ}	t_{PZL}/t_{PLZ}
1.2 V	V_{CC}	50 pF	500 Ω(1)	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	50 pF	500 Ω	open	GND	$2 \times V_{CC}$
3.0 to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

Note

1. The circuit performs better when R_L = 1000 Ω

Definitions for test circuit:

R_L = Load resistor.

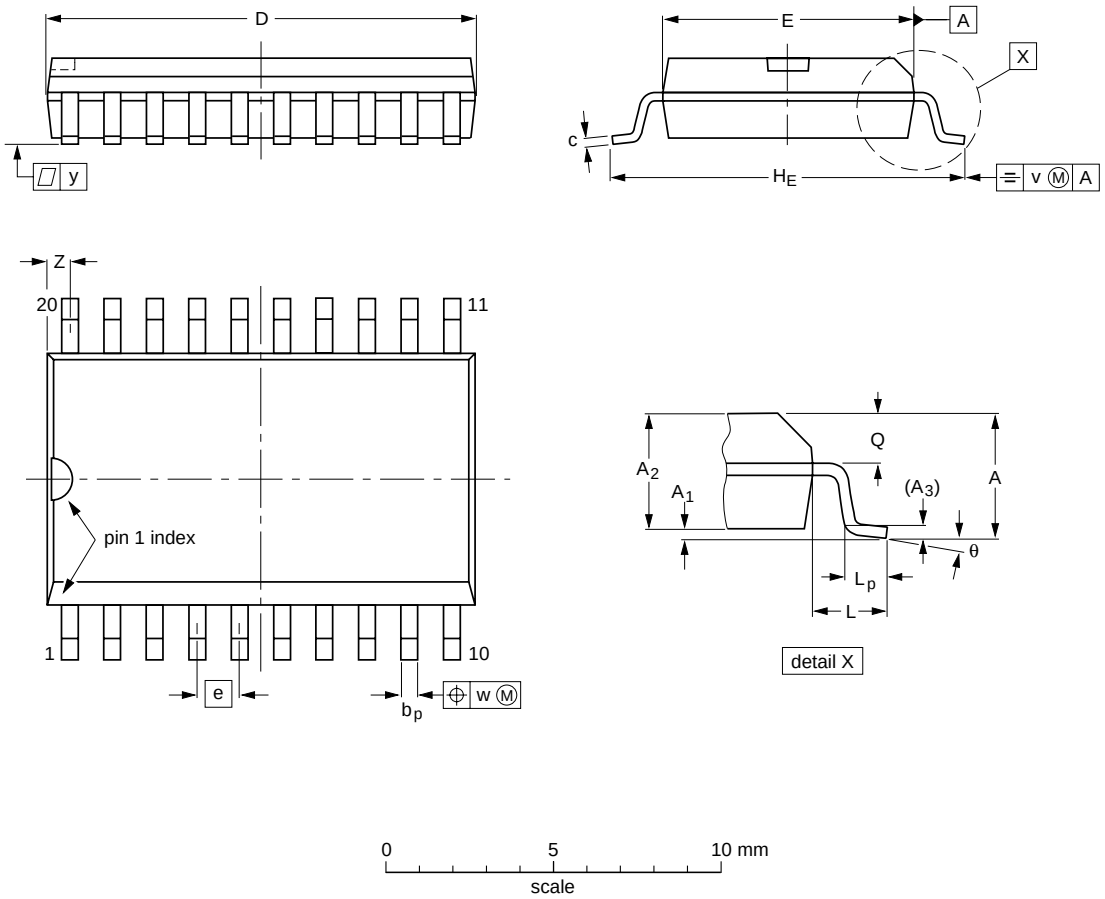
C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

Fig.7 Load circuitry for switching times.

PACKAGE OUTLINES

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

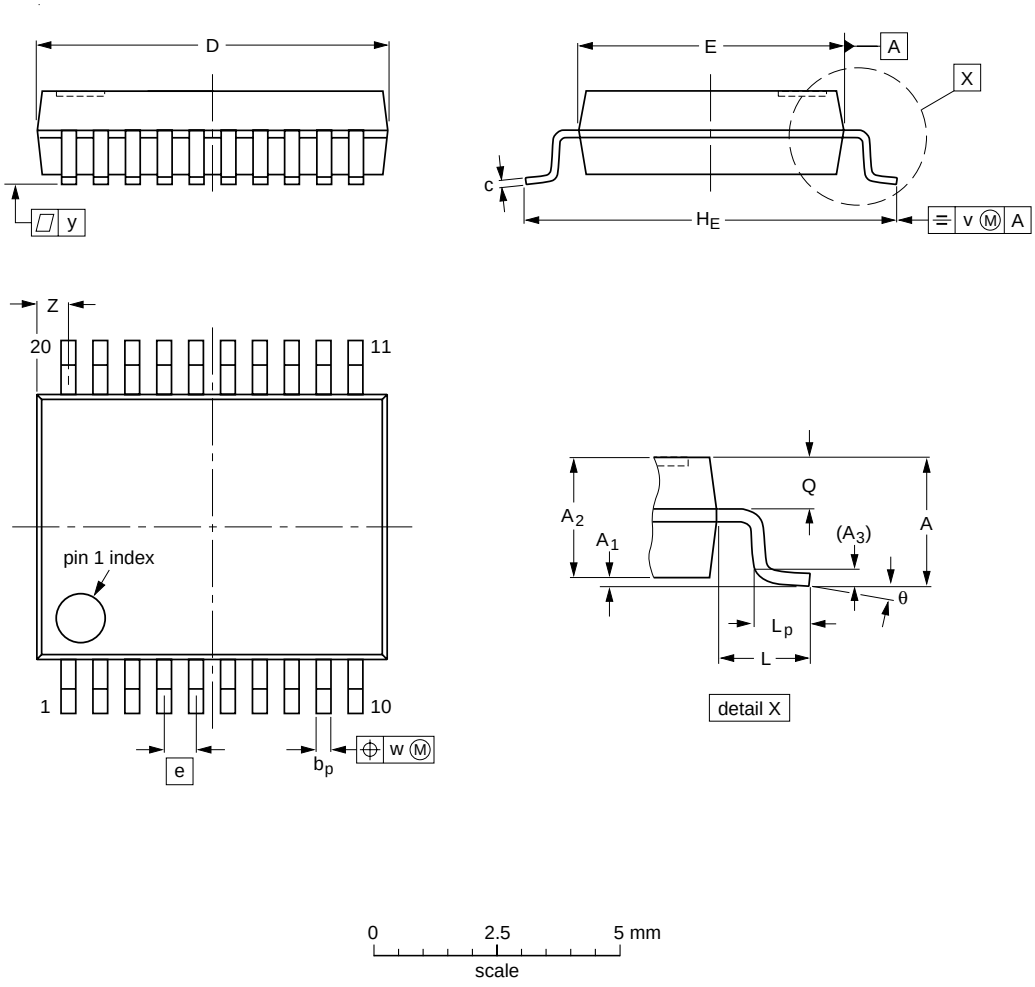
UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT163-1	075E04	MS-013				~~99-12-27~~ 03-02-19

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm **SOT339-1**



DIMENSIONS (mm are the original dimensions)

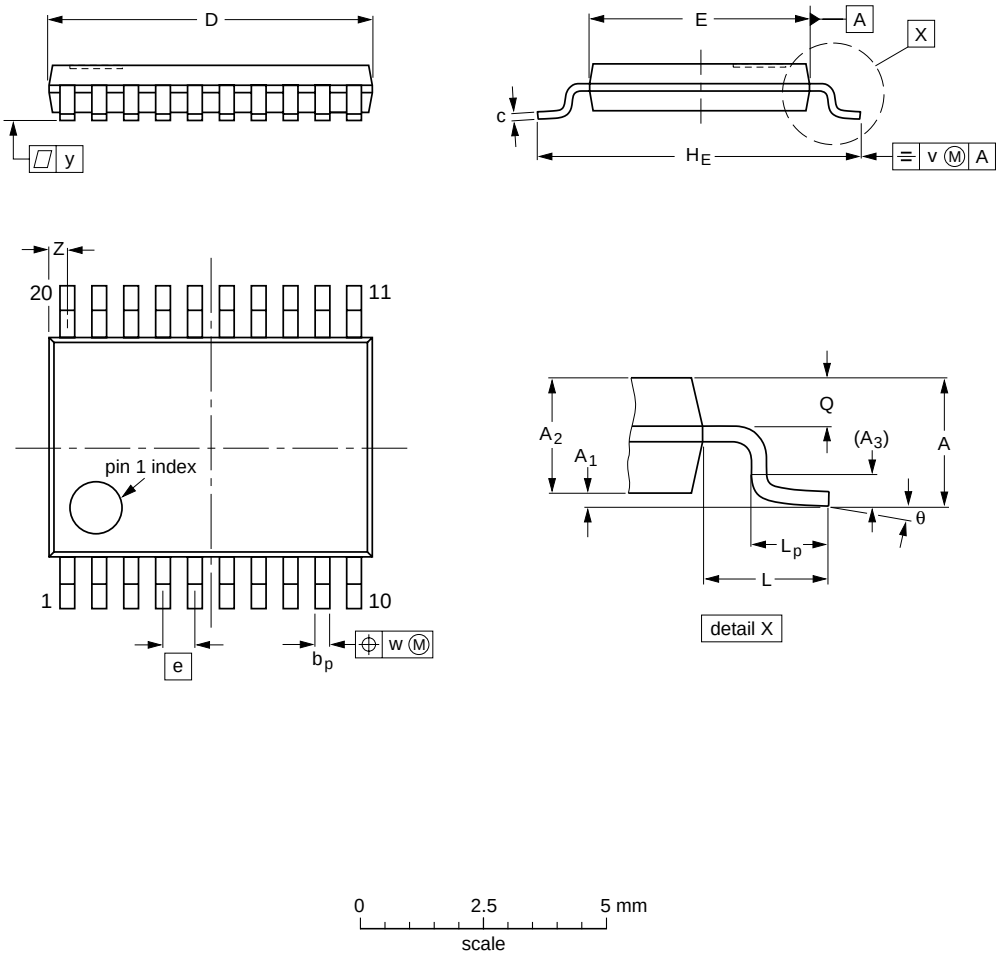
UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8^o 0^o

Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT339-1		MO-150				~~99-12-27~~ 03-02-19

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm **SOT360-1**



DIMENSIONS (mm are the original dimensions)

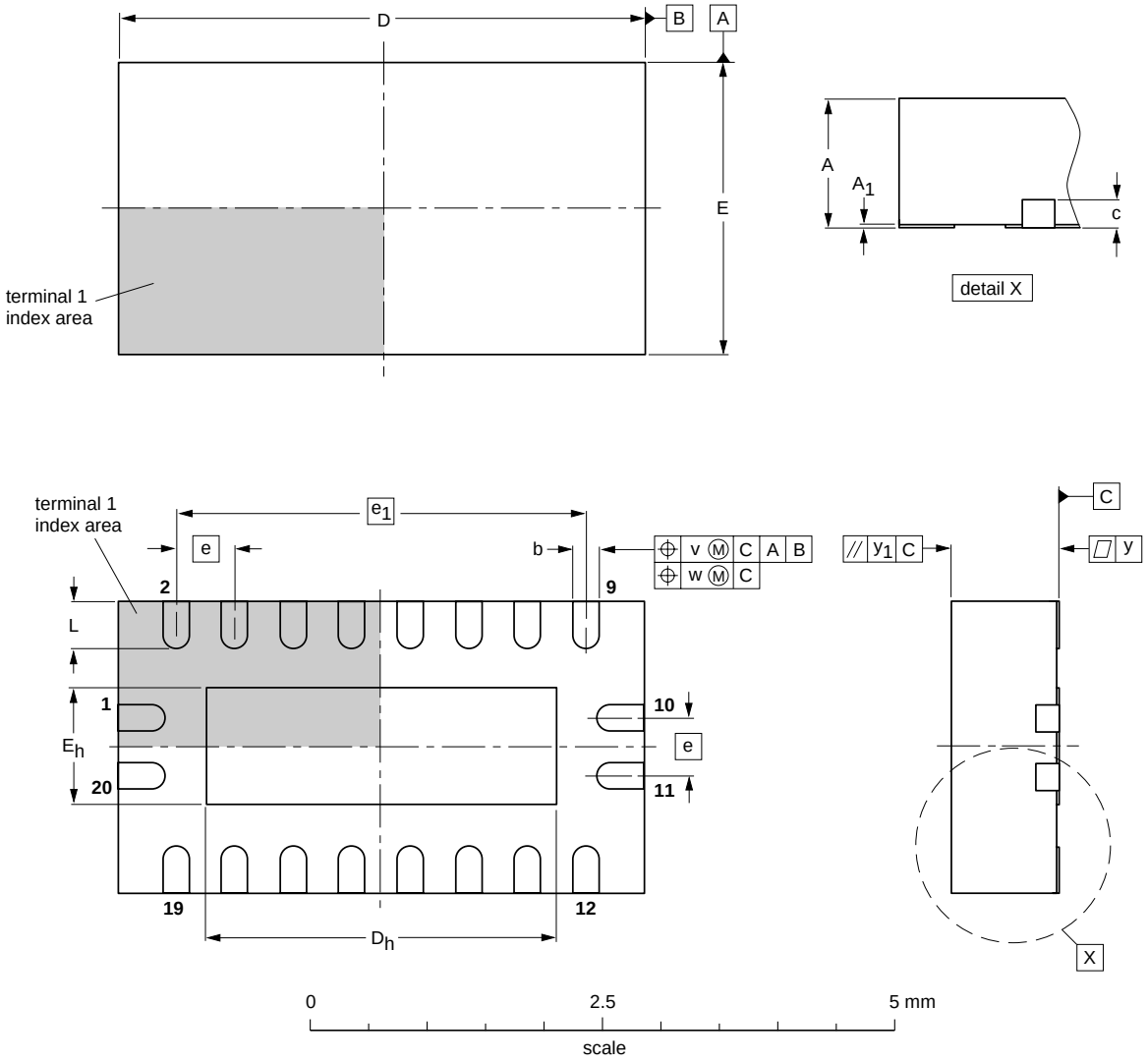
UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT360-1		MO-153				~~99-12-27~~ 03-02-19

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm **SOT764-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	4.6 4.4	3.15 2.85	2.6 2.4	1.15 0.85	0.5	3.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT764-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.
2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status ‘Production’), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

Philips Semiconductors – a worldwide company

Contact information

For additional information please visit **http://www.semiconductors.philips.com**. Fax: **+31 40 27 24825**
For sales offices addresses send e-mail to: **sales.addresses@www.semiconductors.philips.com**.

Printed in The Netherlands 613508/04/pp17 Date of release: 2003 Nov 17 Document order number: 9397 750 10561

Let's make things better.

Philips
Semiconductors

PHILIPS